

## CLAIMS

### What is claimed is:

1. A nonvolatile semiconductor memory device comprising:  
a plurality of sectors;  
each sector comprising memory cell transistors arranged in a cell array block and  
decoder transistors in a column decoder block;  
wherein the transistors in the cell array block and column decoder block in each sector  
share a common bulk region; and  
wherein said semiconductor memory device is configured to electrically erase all the  
memory cell transistors in a sector together.
2. A nonvolatile semiconductor memory device according to claim 1, wherein the  
semiconductor memory device is a NOR-type memory device.
3. A nonvolatile semiconductor memory device according to claim 1, further  
comprising a write driver and a sense amplifier.
4. A nonvolatile semiconductor memory device according to claim 3, wherein the  
write driver and sense amplifier are configured to be placed in a state of high impedance  
during an erase operation to avoid influencing circuit operation during the erase operation.
5. A sector structure of a nonvolatile semiconductor memory, said sector  
structure comprising:  
a plurality of memory cell transistors arranged in a cell array block; and  
a plurality of decoder transistors arranged in a column decoder block, wherein said  
memory cell transistors and decoder transistors are arranged on a common bulk region.
6. A sector structure of a nonvolatile semiconductor memory according to claim  
5, wherein an erase operation is configured to erase all of the transistors in the sector  
simultaneously.
7. A sector structure of a nonvolatile semiconductor memory according to claim  
5, said sector structure further comprising:

a plurality of word lines arranged in the cell array block, each word line being connected to a plurality of cell gates;

a plurality of bit lines arranged in the cell array block, each bit line being connected to a plurality of memory cell drains;

5 a plurality of common data lines connected to the bit lines;

a plurality of write drivers, each connected to a respective one of the common data lines; and

a plurality of sense amplifiers, each connected to a respective one of the common data lines.

8. A sector structure of a nonvolatile semiconductor memory according to claim 7, wherein each write driver and sense amplifier is configured to be placed in a state of high impedance during an erase operation. *Bo*

9. A sector structure of a nonvolatile semiconductor memory according to claim 5, wherein said sector structure is configured to provide 64 Kbytes of memory.

10. A nonvolatile semiconductor memory device, comprising:  
a cell array block comprising a plurality of memory cell transistors having gates and drains, each gate being connected to a corresponding word line out of a plurality of word lines, each drain being connected to a corresponding bit line out of a plurality of bit lines;

a source line driver commonly connected to sources of each memory cell transistor in the cell array block to apply a source voltage;

a plurality of sectors, each sector comprising transistors of a column decoder connected between a plurality of bit lines and common data lines to select one bit line out of the plurality of bit lines; and

a common bulk region arranged in each sector, wherein the memory cell transistors and the column decoder transistors of each sector share the common bulk region; and

a bulk driver provided in each of the sectors, each said bulk driver configured to commonly apply a bulk voltage to the common bulk region of that sector.

11. A nonvolatile semiconductor memory device according to claim 10, wherein the memory device is a NOR-type flash EEPROM.

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12. A nonvolatile semiconductor memory device according to claim 10, wherein the bulk region is a pocket P-well.

5 13. A nonvolatile semiconductor memory device according to claim 10, further comprising a plurality of write drivers and sense amplifiers, wherein each data line is connected to a corresponding one of the write drivers and a corresponding one of the sense amplifiers.

10 14. A nonvolatile semiconductor memory device according to claim 13, wherein the write drivers and sense amplifiers are each configured to be placed in a state of high impedance during an erase operation.

15 15. A nonvolatile semiconductor memory device comprising:  
a plurality of sector units, each sector unit comprising a common bulk region, and wherein each sector unit is configured to be electrically erasable in response to an erase signal; and  
a plurality of memory cell transistors and transistors of a column decoder arranged in the common bulk region of each sector unit and configured to commonly receive a bulk voltage.  
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25 16. A nonvolatile semiconductor memory device according to claim 15, wherein each sector unit further comprises a bulk driver configured to supply a bulk voltage to the common bulk region.

30 17. A nonvolatile semiconductor memory device according to claim 15, wherein said plurality of memory cell transistors are arranged in a cell array block, wherein said plurality of column decoder transistors are arranged in a column decoder block, and wherein said cell array block and said column decoder block are both arranged on the common bulk region.

18. A method of forming a bulk region of a nonvolatile semiconductor device, said method comprising:

forming a bulk region for memory cell transistors provided in a cell array block of the nonvolatile semiconductor memory device; and

forming a bulk region for decoder transistors of a column decoder in the bulk region for the memory cell transistors of the cell array block.

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19. A method of forming a bulk region of a nonvolatile semiconductor device, according to claim 18, further comprising configuring the bulk regions for the memory cell transistors and decoder transistors to receive a common bulk signal during an erase operation.

20. A method of forming a bulk region of a nonvolatile semiconductor device, according to claim 18, wherein said memory cell transistors and said decoder transistors are configured to be simultaneously erased with each other during an erase operation.

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